

Characterization and Comparative Analysis of Structural, Optical and Gas-Sensing Properties of Aluminum-Doped Titanium Dioxide Thin Films

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Abstract: This study examined some physical characterizations of aluminum-doped TiO₂ (TiO₂:Al) nanostructured thin films. Films with 0%, 2%, and 4% Al were deposited via chemical spray pyrolysis (CSP). A polycrystalline tetragonal anatase phase with preferred orientation along the (101) plane was verified by X-ray diffraction. Al³⁺ incorporation enhanced crystallinity, increasing crystallite size from 17.52 nm to 32.38 nm while reducing dislocation density and lattice strain. Atomic force microscopy revealed uniform nanoscale grains, with both particle size and surface roughness decreasing as Al content increased, indicating dopant-induced modifications in nucleation and growth. UV-Vis spectroscopy showed moderate transparency and a reduction in the direct optical band gap from 3.44 eV for undoped TiO₂ to 3.32 eV for 4% Al-doped films, attributed to defect states introduced by Al doping. Higher Al concentration increased electrical resistance but decreased sensitivity in gas-sensing studies toward NO₂ at 140°C, most probably as a result of changed surface adsorption and reduced charge-carrier mobility. Overall, Al doping tunes structural and optical properties effectively, though optimizing the dopant concentration is essential to balance material enhancements with functional gas-sensing performance.

1 INTRODUCTION

TiO₂ is a widely studied material with extensive utilization across diverse fields [1]-[3]. Its utility stems from its high transparency in the visible spectrum combined with a relatively high average refractive index [4]. Moreover, TiO₂ exhibits notable photochromic behavior, making it a material of interest for optical and photonic applications [5]. The intrinsic absorption threshold of titanium dioxide at the blue edge of the visible spectrum, together with its thermodynamic stability, non-toxicity, and cost-effective synthesis of dispersed TiO₂, renders it highly suitable for applications as both a white pigment and a photocatalyst [6], [7]. Chemical reactions involving aluminum and appropriate metal oxides, such as CuO [8], Fe₂O₃ [9], and TiO₂ [10], [11], were widely utilized. These methods leverage the principle that aluminum can reduce these oxides,

generating a different metal alongside aluminum oxide. The metal produced can serve as a beneficial alloying component for the aluminum matrix or can form intermetallic compounds with aluminum that act as reinforcements. Notably, aluminum oxide, particularly Al₂O₃, serves as an effective reinforcement for AMCs [12]. Among the various reactive pairs involving aluminum and metal oxides, the Al-TiO₂ system stands out for its Al₃Ti. At both room temperature and higher temperatures, one of its derivative forms has good mechanical properties [13], [14]. Gas sensors based on titanium dioxide (TiO₂) have been shown to have a high sensitivity and stability under harsh environmental conditions, highlighting their potential as the preferred material for high-temperature gas sensing applications [15]-[17]. TiO₂ exists in three distinct crystalline phases: rutile, anatase, and brookite. Among the three crystalline forms, anatase and rutile are the most

commonly observed, as brookite is relatively unstable [18]. The specific phase of TiO_2 significantly affects its properties, including catalytic activity and gas-sensing performance [19]. In particular, the anatase phase is often favored, especially in reducing environments such as carbon monoxide (CO) detection [20]. Enhancing the surface area of TiO_2 can further improve sensor sensitivity by increasing the number of available surface oxygen sites for gas interactions. Consequently, nanoscale TiO_2 , characterized by a high surface-to-weight ratio, is expected to exhibit superior sensitivity in TiO_2 -based gas sensors [21], [22]. In this study, aluminum-doped TiO_2 nanostructured thin films were synthesized using CSP, which enables the fabrication of homogeneous coatings over large areas [23], [24]. In this work, we investigate the impact of Al doping on some physical characteristics and gas-sensing properties of TiO_2 nanostructured thin films. Various Al concentrations were used to systematically investigate their effects on crystal structure, surface morphology, optical characteristics, and sensing performance. Understanding these effects is vital to optimizing TiO_2 -based materials for potential applications in gas sensor technologies.

2 EXPERIMENTAL

Undoped TiO_2 and aluminum-doped TiO_2 films were deposited via CSP method. 0.1 M of $\text{TiCl}_4 \cdot 5\text{H}_2\text{O}$ was prepared in deionized water, and aluminum, obtained from Sigma-Aldrich (Germany), was used as the doping agent. The solution was mixed with two or three drops of HCl to achieve complete clarity. The deposition was carried out with glass substrate maintained at 400°C , and the spray nozzle positioned 28 cm from the base surface. The spray rate was set to 4 mL/min and the spraying time was 10 s, followed by a 90 seconds wait to prevent substrate cooling. The carrier gas used was nitrogen. The film thickness was measured by weighing and found to be 320 ± 30 nm. AFM was used to examine surface morphology, while XRD was employed to determine crystal structure. Optical transmittance measurements were done via a double-beam Shimadzu UV-VIS spectrophotometer. Gas-sensing measurements were conducted in a cylindrical chamber with a radius of 7 cm and a height of 17 cm.

3 RESULTS AND DISCUSSION

Figure 1 presents the X-ray diffraction (XRD) patterns of the deposited films. The diffraction

patterns exhibit characteristic peaks at 25.22° , 37.85° , 53.63° , and 62.67° , corresponding to the (101), (004), (105), and (220) crystallographic planes of anatase TiO_2 , respectively. The strongest diffraction peak is observed for the (101) plane, indicating the preferential orientation of the crystallites along this direction. These diffraction peaks are in good agreement with ICDD card No. 21-1272, confirming the formation of the anatase crystalline phase. The sharp and well-defined diffraction peaks indicate good crystallinity of the deposited films. Furthermore, the absence of additional diffraction peaks associated with secondary phases or aluminum-containing compounds suggests that Al ions were successfully incorporated into the TiO_2 lattice rather than forming separate phases.

The crystallite size was estimated using the Scherrer method [25], [26], and the calculated values are summarized in Table 1. The crystallite size increased from 17.52 to 32.38 nm with increasing aluminum dopant concentration. This increase indicates enhanced crystal growth and improved crystallinity, which may be attributed to the promotion of grain growth and the reduction of lattice imperfections during film formation.

The dislocation density was calculated from the crystallite size [27], [28]. As shown in Table 1, the dislocation density decreased from 39.56 to 25.27 with increasing aluminum concentration, indicating an improvement in crystal quality due to the reduction of structural defects within the crystal lattice.

The lattice strain was also determined from the XRD peak broadening [29], [30]. As presented in Table 1, the strain decreased from 29.79 to 20.14 as the aluminum dopant concentration increased, suggesting relaxation of internal lattice stresses and improved structural ordering. Figure 2 illustrates the variation of the structural parameters, including crystallite size, dislocation density, lattice strain, and full width at half maximum (FWHM), while Table 1 summarizes the corresponding FWHM values used in the structural analysis.

Figure 3 presents the atomic force microscopy (AFM) images of TiO_2 and Al-doped TiO_2 thin films. The surface morphology shows nanoscale grains uniformly distributed across the films, confirming the formation of nanostructured layers. The average particle sizes P_{av} were determined to be 84.1 nm, 67.8 nm, and 46.2 nm for undoped TiO_2 , TiO_2 :2% Al, and TiO_2 :4% Al, respectively, while the corresponding root mean square (RMS) roughness values were 9.23 nm, 6.05 nm, and 4.67 nm. The average surface roughness (R_a) decreased from 7.37 nm to 3.65 nm with increasing Al content. This increment in particle size and surface roughness is attributed to the effect of Al ions on nucleation and

growth, resulting in a more compact, uniform film surface. The AFM parameters A_{para} , including particle size, Ra, and RMS roughness, are summarized in Table 2, highlighting the significant role of Al doping in enhancing surface morphology.

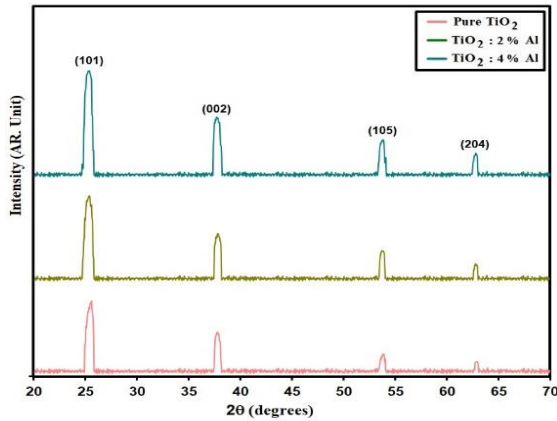


Figure 1: XRD patterns of undoped and Al-doped TiO_2 thin films.

Figure 4 shows the variation of transmittance (T); The findings show that the films have an average

amount of optical transparency in the visible spectrum, with transmittance values ranging from 74.3% to 78.1%. Furthermore, the transmittance increases gradually with the longer wavelength. This increase in transmittance at higher wavelengths indicates reduced light absorption in the near-infrared region, mainly due to lower photon energy, which is insufficient to excite electrons across the band gap. Such behavior is typical of wide-band-gap semiconductor materials like TiO_2 , where absorption is stronger in the ultraviolet and decreases toward the visible and infrared regions [31], [32].

The absorbance (A) of the films was determined from the transmittance (T), based on the incident light intensity (I_0) and the transmitted light intensity (I) [33], [34].

As illustrated in Figure 5, the pure TiO_2 film exhibits the lowest absorbance, whereas the TiO_2 films doped with 2% and 4% aluminum display progressively higher absorbance values. This increase in absorbance can be assigned to the incorporation of Al into the TiO_2 lattice, which introduces additional defect states and impurity energy levels within the band gap. These localized states enhance the probability of electronic transitions and facilitate the absorption of incident photons [35], [36].

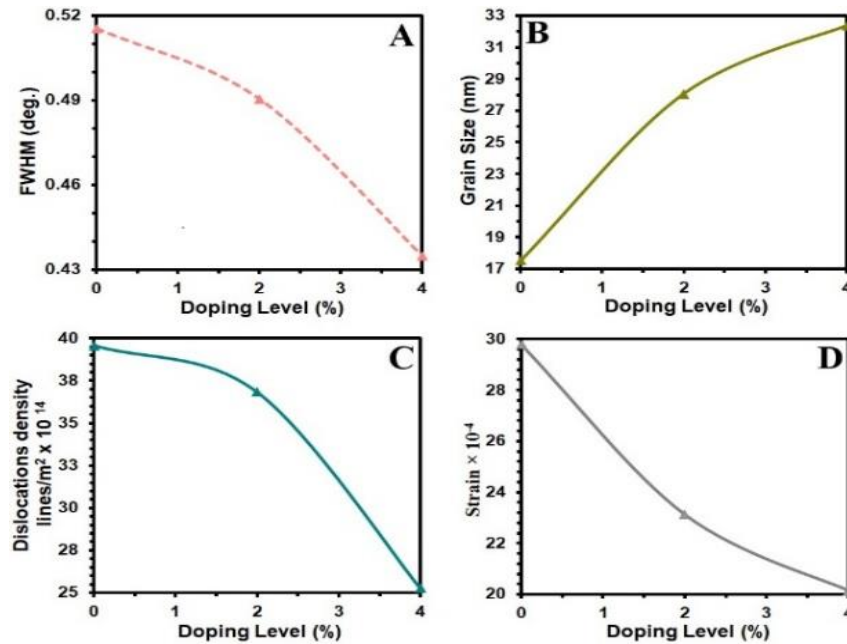


Figure 2: Variation of the structural parameters of undoped and Al-doped TiO_2 thin films.

Table 1: Structural parameters and optical band gap of undoped and Al-doped TiO_2 thin films.

Specimen	(hkl) Plane	2 θ (°)	FWHM (°)	E_g (eV)	D (nm)	δ ($\times 10^{14}$) (lines/m ²)	ε ($\times 10^{-4}$)
Undoped TiO_2	101	25.23	0.52	3.44	17.52	39.56	29.79
TiO_2 : 2% Al	101	25.20	0.49	3.38	28.67	36.82	23.12
TiO_2 : 4% Al	101	25.16	0.44	3.32	32.38	25.27	20.14

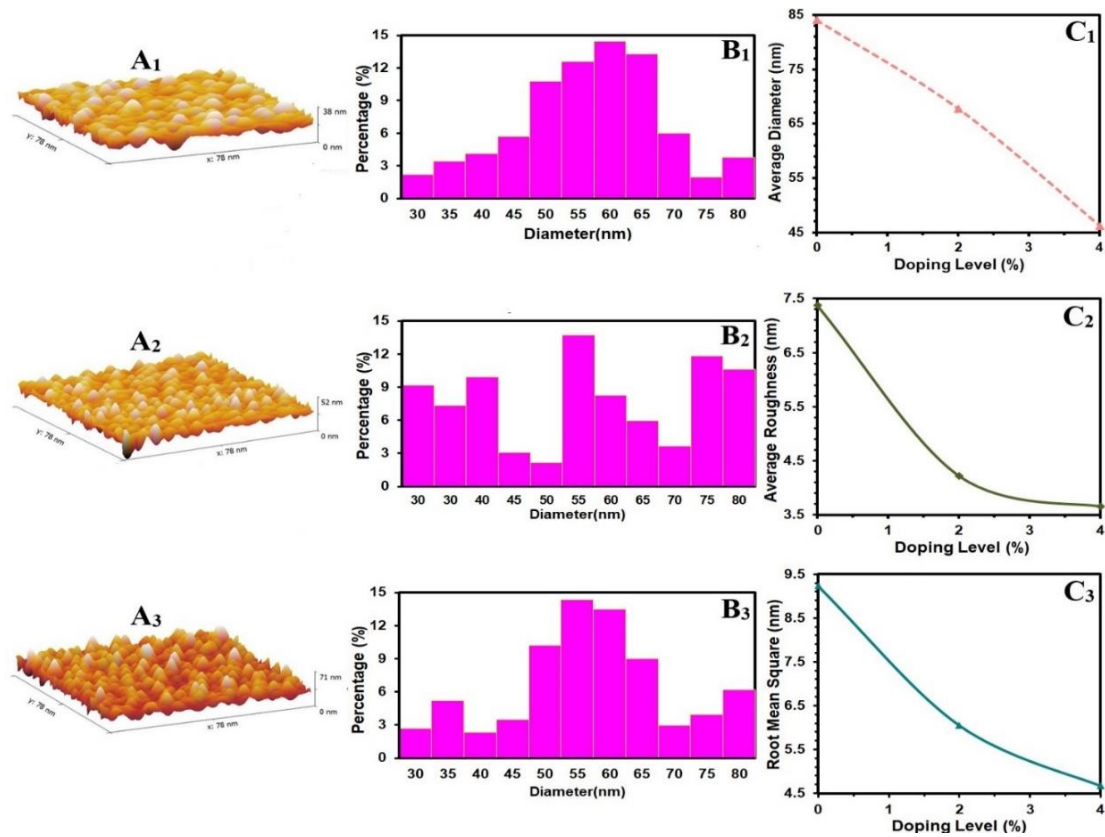
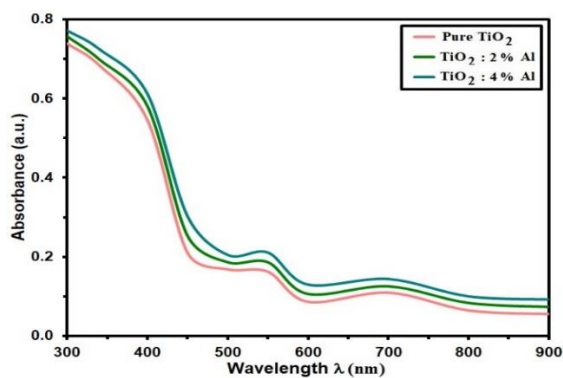

 Figure 3: AFM surface images of undoped and Al-doped TiO_2 thin films.

 Table 2: AFM surface morphology parameters of undoped and Al-doped TiO_2 thin films.

Sample	P_{av} (nm)	R_a (nm)	rms (nm)
TiO_2	46.2	3.65	4.67
TiO_2 : 2% Al	67.8	4.22	6.06
TiO_2 : 4% Al	84.1	7.37	9.23


 Figure 4: Optical transmittance spectra of undoped and Al-doped TiO_2 thin films.

The absorption coefficient (α) of the films was calculated from the absorbance and film thickness (t) [37].

Figure 6 illustrates the variation of α with photon energy ($h\nu$) for undoped and Al-doped TiO_2 thin films. The results indicate that α increases with higher aluminum doping concentrations, particularly near the absorption edge, where a sharp rise reflects strong optical absorption due to electronic transitions from the valence band (VB) to the conduction band (CB). At higher photon energies, α gradually decreases. The absorption coefficient reaches values on the order of 10^4 cm^{-1} , confirming pronounced optical absorption and suggesting dominant direct electronic transitions within the band structure. The enhancement of α with Al doping is attributed to modifications in the electronic structure, in which Al incorporation introduces additional defect states and localized energy levels within the band gap, thereby improving the films' photon-absorption capability [38], [39].

The films' direct band gap (E_g) was calculated using the Tauc relation between the absorption coefficient and photon energy, with $n = 1/2$ corresponding to allowed direct transitions [40], [41].

As shown in Figure 7, E_g of TiO_2 thin films diminishes with rising aluminum doping concentration. This reduction is credited to the creation of defect states and impurity levels within E_g caused by Al incorporation, which introduces additional energy levels between VB and CB, enabling electronic transitions at lower $h\nu$. Consequently, E_g narrows from 3.44 eV for undoped TiO_2 to approximately 3.32 eV for the highest Al-doped films. Increased structural disorder and defect density due to Al doping further contribute to band tailing and effective band gap narrowing [42], [43].

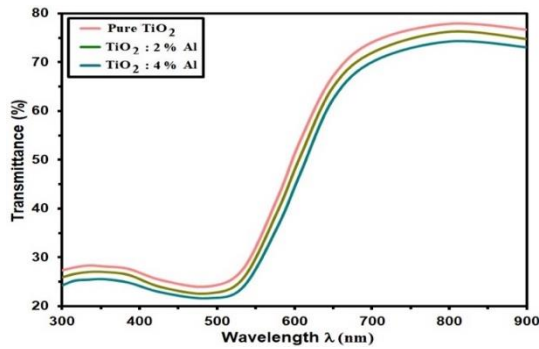


Figure 5: Optical absorbance spectra of undoped and Al-doped TiO_2 thin films.

The extinction coefficient (k) was evaluated from the absorption coefficient (α) and wavelength (λ) [44], [45].

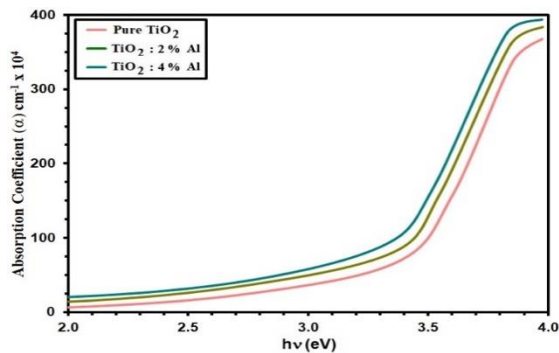


Figure 6: Absorption coefficient (α) as a function of photon energy ($h\nu$) for undoped and Al-doped TiO_2 thin films.

Figure 8 shows the variation of k with λ . The results indicate that k increases rapidly in the ultraviolet (UV) region and then gradually decreases with increasing wavelength. This behavior is related to the material's optical absorption properties. The nonzero values of k below the fundamental absorption edge indicate sub-band-gap absorption, which is mainly attributed to defect states, impurity levels, and localized energy states within the band gap

caused by structural imperfections or dopant incorporation [46].

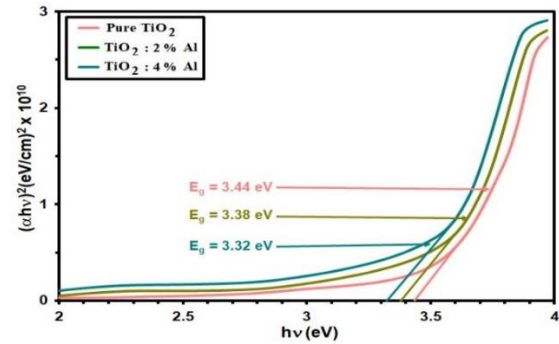


Figure 7: Tauc plots for determining the optical band gap (E_g) of undoped and Al-doped TiO_2 thin films.

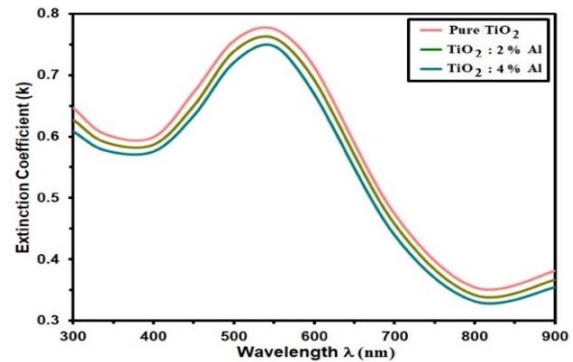


Figure 8: Extinction coefficient (k) spectra of undoped and Al-doped TiO_2 thin films.

The refractive index (n), which describes the propagation of light within the material, was determined from the reflectance (R) and extinction coefficient (k) [47], [48].

Figure 9 shows n of TiO_2 thin films as a function of λ . For all Al-doped films, n increases with wavelength but decreases with higher Al content. This reduction is attributed to changes in electronic polarizability and structural modifications caused by Al incorporation, including lattice distortions and reduced film density [49], [50], [59].

The gas-sensing performance was evaluated at 140°C , and Figure 10 shows the resistance variation of the TiO_2 films exposed to 225 ppm NO_2 . Undoped TiO_2 exhibited the lowest resistance, indicating efficient NO_2 adsorption and high charge carrier mobility [51], [52]. In contrast, TiO_2 doped with 4% Al showed the highest resistance, likely due to dopant-induced modifications in the electronic structure that hinder charge transport and alter surface interactions with NO_2 molecules. These results demonstrate that Al doping increases the resistance

and significantly affects the gas-sensing behavior of TiO_2 films [53], [54].

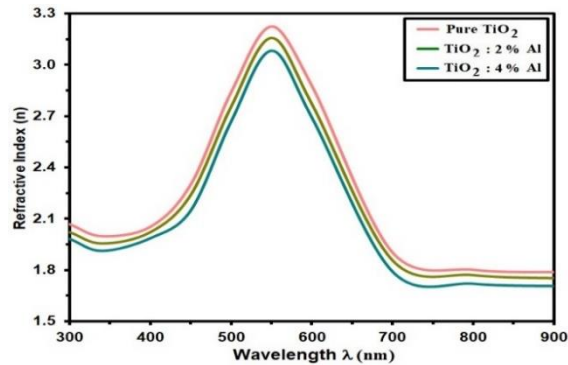


Figure 9: Refractive index (n) spectra of undoped and Al-doped TiO_2 thin films.

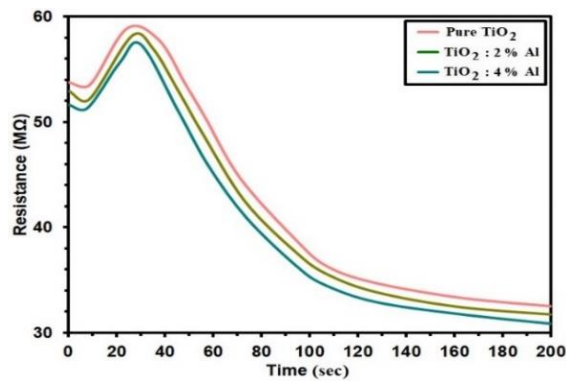


Figure 10: Resistance response of undoped and Al-doped TiO_2 thin films to 225 ppm NO_2 at 140 °C.

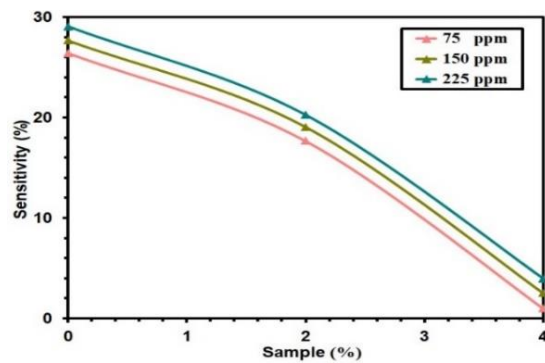


Figure 11: Gas sensitivity of undoped and Al-doped TiO_2 thin films toward NO_2 .

The sensitivity (S) was calculated from the relative change in resistance between air and gas exposure, where R_g and R_a represent the resistance of the film sensor in the presence of gas and in air, respectively [55].

Figure 11 shows S of TiO_2 , TiO_2 :2% Al, and TiO_2 :4% Al thin films toward NO_2 gas. The results show that sensitivity decreases with increasing Al doping, reflecting enhanced carrier recombination and reduced sensor response. Specifically, at 75, 150, and 225 ppm NO_2 , the sensitivity drops from 26.42% to 1.01%, 27.65% to 2.52%, and 29.06% to 3.96%, respectively. This decline is attributed to dopant-induced structural modifications that hinder charge-carrier mobility, thereby diminishing the films' gas-sensing performance [56]-[58].

4 CONCLUSIONS

Aluminum-doped TiO_2 nanostructured films were successfully created via chemical spray pyrolysis. The structural analysis verified a single-phase anatase structure in all films, signifying substitutional incorporation of Al^{3+} ions into the TiO_2 lattice. This incorporation significantly influenced the microstructural properties: crystallite size rose, while both dislocation density and lattice strain rose with higher Al content, indicating improved overall crystalline quality. Morphologically, Al doping led to a smoother, more compact surface, as both the average particle size and surface roughness were increased. Optically, the films remained highly transparent. The decrease in E_g with rising Al content is a key finding, proposing that doping can be used to tailor the light absorption edge of TiO_2 for specific optoelectronic applications. However, the gas-sensing results for NO_2 revealed a complex trade-off. While Al doping increased the films' baseline resistance, it concurrently reduced their sensitivity.

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